

L Number	Hits	Search Text	DB	Time stamp
1	1	"112'0965"	CPO;	2003/06/13 14:36
2	0	"ipi1250965"	JPN;	2003/06/13 15:01
3	0	643347.pn. and (sealing plate).clm.	JPN;	2003/06/13 15:01
4	0	643347.pn. and (adhesive sealing plate).clm.	JPN;	2003/06/13 15:01
5	0	643347.pn. and (sealing plate).clm.	USPAT	2003/06/13 15:01
6	1	643347.pn.	USPAT	2003/06/13 15:53
7	0	pate.-ashok.xp. and preferred adj embodiments	USPAT	2003/06/13 15:53
8	0	patel-ashok.xp. and preferred adj embodiments	USPAT	2003/06/13 15:53
-	229	(445/25).CCLS.	USPAT	2003/06/14 14:34
-	343	(313/512).CCLS.	USPAT	2003/06/14 14:34
-	0	09671654.ap.	US-PGPUB; EPO; CPO; DEGWENT; IBM_TDB	2003/06/14 14:34
-	1	9671654.ap.	USPAT;	2001/08/18 14:33
-			US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	
-	229	(445/25).CCLS.	USPAT	2001/08/18 14:43
-	722	((313/512) or (445/25)).CCLS.	USPAT;	2001/08/18 14:43
-	17	((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT;	2001/08/18 14:55
-	13	((313/512) or (445/25)).CCLS.) and active adj matrix) and crystal	USPAT;	2001/08/18 14:56
-	1	((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT;	2001/08/18 14:58
-	3	5672183.JEPN.	USPAT	2001/08/18 14:57
-	1	((313/512) or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT	2001/08/18 15:01
-	0	(257.\$).ccls.	USPAT;	2001/08/18 15:01
-			US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	
-	134751	(257.\$).ccls.	USPAT;	2001/08/18 15:02
-			US-PGPUB; EPO; CPO; DEGWENT; IBM_TDB	
-	66945	(313/5).ccls.	USPAT;	2001/08/18 15:02
-	8	i(2:7/5).ccls.) and active adj matrix and organic with EL) and gate with (field adj effect adj transistor FET)	USPAT;	2003/08/18 15:04
-			US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	

	3	(257/3).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:32
	0	(313/3).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:25
-	4347	(257/7) or (257/5) or (257/6) or (257/6*) or (257/2 or (257/34) or (257/35)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 16:14
-	2	(257/37) or (257/39 or (257/36) or (257/50) or (257/17) or (257/41) or (257/34)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 08:36
-	4396	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/13 10:58
-	4178	yamazaki-shunpei.in.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/13 15:31
-	943	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT	2003/06/11 18:06
-	1171	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB	2002/06/13 15:32
-	0	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/08/13 15:33
-	1	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/08/13 15:33
-	3	10895*.URPN.	USPAT	2003/08/18 15:35
-	2	(257/37) or (257/59) or (257/66) or (257/6*) or (257/72) or (257/34) or (257/35)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET mostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/08/18 16:15
-	5136	(257/37) or (257/39) or (257/66) or (257/3*) or (257/11) or (257/34) or (257/35)) or (257/11) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/08/19 13:56
-	2	(257/37) or (257/5*) or (257/66) or (257/3*) or (257/11) or (257/34) or (257/35) or (257/30) or (257/11) or (445/25)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET mostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/08/18 16:15
-	2	("616_893" "6246_71").PN.	USPAT	2002/08/28 16:27
-	5150	((257/57) or (257/59 or (257/66) or (257/6*) or (257/71) or (257/37) or (257/35) or (313/51) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 10:00

3	("6351010").PN.	USPAT; US-FGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 07:37
2	("6153833" "6246070").PN.	USPAT	2002/08/29 07:47
0	((("6153-33" "6246070").PN.) and organic with EL electroluminescence electro luminescent.	USPAT	2002/08/29 07:46
0	((("6153-33" "6246070").PN.) and organic same EL electroluminescence electro luminescent	USPAT	2002/08/29 07:46
3	semiconductor-energy-laboratory.as.	USPAT	2002/08/29 07:48
4	semiconductor-energy-laboratory.is.	USPAT	2002/08/29 07:51
7	single.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 07:55
3	single.as. and singl. adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and organic with (EL electroluminescence)	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:00
0	single.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and organic with (EL electroluminescence). and invert	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:00
2	(1(257/57) or (257/50) cr (157/6) or (157/61) cr (257/7) cr (257/34) or (257/31) or (313/51) cr (445/15)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:38
2	(1(257/57) or (257/50) cr (157/6) or (157/61) or (257/7) or (157/34) or (257/31) or (313/51) cr (445/15)).CCLS.) and active adj matrix and (organic with EL electroluminescence) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:43
3	(1(257/57) or (257/50) cr (157/6) or (157/61) cr (157/7) or (257/34) or (257/31) cr (313/51) cr (445/15)).CCLS.) and active adj matrix and (organic with EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate t.p adj gate) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:44
8	(1(257/57) or (257/50) cr (157/6) or (157/61) or (257/7) or (257/34) or (257/31) or (313/51) cr (445/15)).CCLS.) and active adj matrix and (organic with EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate t.p adj gate) and single adj crystal and ja	USPAT; US-PGPUB; EPO; JPO; DEFVENT; IBM_TDB	2002/08/29 08:44

5 (((257/57) or (257/59) or (257/61) or
 (257/63) or (257/72) or (257/74) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and active adj matrix and (organic with
 (EL) : electroluminescence
 effect; luminescent) and gate with (field
 effect; adj transistor FET : bottom adj
 gate : p adj gate) and single adj crystal
 and inert adj gas
 80 ((257/57) or (257/59) or (257/61) or
 (257/63) or (257/72) or (257/74) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and TFT with TFT
 1 6074-1.PPN.
 14 ("5.4/190" | "5610402" | "5401162"
 "5610403" | "5610404" | "5610405" |
 "5610406" | "5710406" | "5710407" |
 "5710408" | "5710409" | "5910402" |
 "5910403" | "5960403").PN.
 0 ("5.4/190" | "5610402" | "5401162" |
 "5610403" | "5610404" | "5610405" |
 "5610406" | "5710406" | "5710407" |
 "5710408" | "5710409" | "5910402" |
 "5910403" | "5960403").PN. and : active adj
 matrix and (organic with : EL
 effect; luminescence electroluminescent))
 and gate with : field adj effect adj
 transistor FET : bottom adj gate : p adj
 gate) and single adj crystal and inert
 adj gas
 0 ("5.4/190" | "5610402" | "5401162"
 "5610403" | "5610404" | "5610405" |
 "5610406" | "5710406" | "5710407" |
 "5710408" | "5710409" | "5910402" |
 "5910403" | "5960403").PN. and : active adj
 matrix and (organic with : EL
 electroluminescence electroluminescent))
 and gate and single adj crystal and
 (inert adj gas)
 492 ((257/57) or (257/59) or (257/61) or
 (257/63) or (257/71) or (257/73) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and inert gas with organic adj : EL
 9 ((257/57) or (257/59) or (257/61) or
 (257/63) or (257/71) or (257/73) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and inert adj gas with organic adj : EL same
 oxide
 0 ((257/57) or (257/59) or (257/61) or
 (257/63) or (257/71) or (257/73) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and inert adj gas same organic adj : EL same
 oxide determine
 0 ((257/57) or (257/59) or (257/61) or
 (257/63) or (257/71) or (257/73) or
 (257/76) or (317/512) or (445/13)).CCLS.)
 and active adj matrix and (organic with
 : EL electroluminescence
 effect; luminescent) and gate with : field
 effect; adj transistor FET : bottom adj
 gate (p adj gate) and single adj crystal
 and rare adj gas)

- 8 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/247) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1
 3 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/34) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1
 3 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/34) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1
 3 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/34) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1
 1 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/34) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1 and barium id oxide
 silica gel drying
 1 ((1257/57) or (257/59) or (257/66) or
 (257/66) or (257/11) or (257/34) or
 (257/356) or (313/312) or (445/25)).CCLS.)
 and active adj matrix and (organic with
 (EL electroluminescence)) and
 electroluminescent and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate and single adj crystal
 and helium he argon ar krypton kr xenon
 xe nitrogen n1 and helium he argon ar
 krypton kr xenon xe nitrogen n1 and
 barium adj oxide silica adj gel drying)

1	(11-257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/260) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL + electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and helium he argon ar krypton kr xenon xe nitrogen n:) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas inert adj gas and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 10:29
1	(11-257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/260) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL + electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and helium he argon ar krypton kr xenon xe nitrogen n:) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 11:14
4	(11-257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/260) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL + electroluminescence electroluminescent) and field adj effect adj transistor FET bottom adj gate top adj gate and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 11:20
1	(11-257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/260) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL + electroluminescence electroluminescent) and field adj effect adj transistor FET bottom adj gate top adj gate and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 11:15
4	(11-257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/260) or (313/512) or (445/25)).CCLS.) and matrix and organic with EL + electroluminescence electroluminescent) and field adj effect adj transistor FET (bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/06/12 14:12
1075	313 54	USPAT; US_PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 11:58
	0 313 514,500	USPAT; US_PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 11:58
	1650 313 514 313 500	USPAT; US_PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 12:20
	1075 313 514	USPAT; US_PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 12:21
	1064 (313 504; or (313/500)).CCLS.	USPAT; US_PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 12:36

116	((313/504; or (313/500)).CCLS.) AND Active adj matrix	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:21
114	((((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet))	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:23
9	(((((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet)) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 13:32
7	(((((313/504; or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet)) and single adj crystal) and (inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n))	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:28
7	((((313/504; or (313/500)).CCLS.) AND Active adj matrix) and field effect transistor fet) and single adj crystal) and (inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n))	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:36
0	2001-08/29 12:36.USIN.	USPAT	2001-08/29 13:36
810	((313/504) or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 13:37
530	((313/504) or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:38
407	((313/504) or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:39
2	((313/504; or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen) same envelope vacant vacancy and organic adj EL organic adj layer	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:40
181	((313/504) or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen) and organic adj EL organic adj layer and barium adj oxide silica gel	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:41
57	((313/504) or (313/500)).CCLS.) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen) same barium adj oxide silica gel and organic adj EL organic adj layer	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:44
615	((313/504) or (313/500)).CCLS.) and barium adj EL organic adj layer	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:44
57	((313/504) or (313/500)).CCLS.) and organic adj EL organic adj layer) and inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen) same barium adj oxide silica gel	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:45
57	((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer) and (inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen) same barium adj oxide silica gel	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2001-08/29 12:47

46	((313/564) or (313/566)).CCLS.) and (organic adj EL organic adj layer)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 13:33
10	((((313/564) or (313/566)).CCLS.) AND Active adj matrix and field effect transistor fet) and single adj crystal monocrystalline non-crystalline) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 13:32
0	((((313/564) or (313/566)).CCLS.) AND Active adj matrix and field effect transistor fet) and single adj crystal monocrystalline non-crystalline) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 13:53
3	((((313/564) or (313/566)).CCLS.) AND Active adj matrix and field effect transistor fet) and single adj crystal monocrystalline non-crystalline) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 13:54
008	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495)).CCLS.	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 13:57
0	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495). and active adj matrix and FET field adj effect adj transistor) same organic adj EL and (barium adj oxide silica adj gel and titanium he nitrogen krypton kr argon ar xenon xe	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 14:00
1	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495). and active adj matrix and FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 14:01
1	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495).CCLS.. and active adj matrix and FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 14:03
1	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495).CCLS.. and active adj matrix and FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 14:03
1	((217/17) or (217/21) or (217/47) or (217/48) or (217/71) or (217/84)) or (217/85) or (313/12) or (445/5) or (313/50) or (313/504) or (313/495).CCLS.. and active adj matrix and FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US_PGPUB; EPO; CPC; DEFWENT; IBM_TDB	2002/08/29 14:03

	1 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence and barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB	2002/08/29 14:23
	2 ("6175186").PM.	USPAT; US-PGPUE; EPO; CPC; DEGWENT; IBM_TDB	2002/08/29 14:04
	24 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUE; EPO; CPC; DEGWENT; IBM_TDB	2002/08/29 14:06
	10 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUE; EPO; CPC; DEGWENT; IBM_TDB	2002/08/29 14:27
	1 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (ogolek)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2002/08/29 14:35
	1 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence and barium adj oxide silica adj gel)	USPAT; US-PGPUB	2002/08/29 14:23
	1 ("257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	JPO	2002/08/29 14:24
	15 ("257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2002/08/29 15:53
	537 ("1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/360) or (313/512) or (445/25) or (313/540) or (313/564) or (313/455)).CCLS.; and organic with (EL electroluminescent electroluminescence and helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DEGWENT; IBM_TDB	2002/08/29 14:36

	11	((1257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/306) or (313/934) or (313/495)).CCLS., and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel and degasse	USPAT; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 14:41
-	0	jp10730165	JP	2002/08/29 14:42
-	0	semiconductor adj laboratory and yamazaki and "1358"	JP	2002/08/29 14:43
-	5179	yamazaki and "1358"	JP	2002/08/29 14:43
-	0	yamazaki and "1358" and semiconductor adj energy adj laboratory	JP	2002/08/29 14:43
-	0	"10-3170-5" and yamazaki	JPO	2002/08/29 14:46
-	0	"110-3170-5" and yamazaki	JP	2002/08/29 14:46
-	0	"110-3170-5" and yamazaki	DEWENT	2002/08/29 14:46
-	0	"jp10730165" and yamazaki	JP	2002/08/29 14:46
-	0	"jp10730165" and yamazaki	JPO	2002/08/29 14:46
-	0	"jp10730165" and yamazaki	DEWENT	2002/08/29 14:46
-	0	"jp10730165"	JP	2002/08/29 14:46
-	0	"jp10730165"	JPO	2002/08/29 14:46
-	0	"jp10730165"	DEWENT	2002/08/29 14:46
-	0	"jp10730165"	IBM_TDB	2002/08/29 14:46
-	368	((1257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/306) or (313/934) or (313/495)).CCLS., and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel	USPAT; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 14:50
-	83	((1257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/306) or (313/934) or (313/495)).CCLS., and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel	USPAT; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 14:51
-	36	((1257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/306) or (313/934) or (313/495)).CCLS., and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) same barium adj oxide silica adj gel	USPAT; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 14:52
-	3	((1257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/306) or (313/934) or (313/495)).CCLS., and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) same barium adj oxide	USPAT; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 14:55
-	7	("5739454" "5747320" "5834334" "5837713" "6046543" "6246175" "6307324").PN.	USPAT	2002/08/29 14:54
-	2	("6175186").PN.	USPAT; UC-PGPUB; EPO; JPO; DEWENT; IBM_TDB	2002/08/29 15:13

	0 ((313/\$ and ceramic with transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
	0 ((313/\$ and ceramic same transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
	0 ((313/\$ and ceramic same clear).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
	66966 (313.\$).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/19 15:27
	0 ((313/\$).CCLS.) and nitride adj ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/19 15:28
	359 ((313,\$).CCLS.) and ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/19 16:50
	0 ((313/57) or (257/50) or (257/66) or (257/67) or (257/70) or (257/34) or (257/35) or (313/51) or (445/25) or (313/50) or (313/504) or (313/495).CCLS.) and active adj matrix withoggle	USPAT	2002/08/19 15:54
	24 ((313/57 or (257/50) or (257/66) or (257/67) or (257/70) or (257/34) or (257/35) or (313/51) or (445/25) or (313/50) or (313/504) or (313/495).CCLS.) and display withoggle	USPAT	2002/08/19 15:59
	0 JPL/00163	JPO	2002/08/19 15:58
	0 JPL/00165	JPO	2002/08/19 15:58
	25 ((313/57 or (257/50) or (257/66) or (257/67) or (257/70) or (257/34) or (257/35) or (313/51) or (445/25) or (313/50) or (313/504) or (313/495).CCLS.) and display same poggle	USPAT	2002/08/19 15:59
	26 ((313/57 or (257/50) or (257/66) or (257/67) or (257/70) or (257/34) or (257/35) or (313/51) or (445/25) or (313/50) or (313/504) or (313/495).CCLS.) and display and poggle	USPAT	2002/08/19 16:46
	9 nitride adj ceramic with (transparent clear)	USPAT	2002/08/19 16:47
	9 nitride adj ceramic with oxide with glass with (transparent clear)	USPAT	2002/08/19 16:47
	23 ((313/5).CCLS.) and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 16:52
	0 ((313/4).CCLS. and nitride adj ceramic same (transparent clear))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 16:51

26	((313/\$).CCLS.) and nitride with ceramic same (display clear transparent transparency)	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:07
0	jp1(2854476	JP	2002/08/29 17:07
0	jp12654476	JP	2002/08/29 17:07
0	jp0102854476	JP	2002/08/29 17:12
3	("6251010").PN.	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:13
0	("1459 and yamanaka and insulated adj gate").PN.	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:13
8	((157/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/458)).CCLS.) and yamanaka and insulated adj gate	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:16
0	((157/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/458)).CCLS.) and insulated adj gate and organic adj layer	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:17
3	spongy. and insulated adj gate adj field and organic	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2002/08/29 17:18
389	yamazaki-shunpei.in. or arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
22	yamazaki-shunpei.in. and arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
21	yamazaki-shunpei.in. and arai-yasuyuki.in. and organic	US-PGPUB	2003/06/12 11:17
9	"passivation film 847"	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 10:56
0	"passivation film 847 is formed on the anode layer 846"	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 11:01
0	"passivation film 847 is formed on the anode layer 846."	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 10:57
1420	semiconductor adj device adj method adj fabricating	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 11:00
745	semiconductor adj device adj method adj fabricating.ti.	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 11:01
0	"passivation film 847 is formed"	USPAT; US-PGPUB; EP; JPO; DEGWENT; IBM_TDB	2003/06/12 11:02
0	yamazaki-shunpei.in. and arai-yasuyuki.in. and miakami-satoshi.in.	US-PGPUB	2003/06/12 11:18

	: yamazaki-shimpei.in, and arai-yasuyuki.in, ani murakami-satoshi.in.	US-PGPUB	2003/06/12 11:18
2171	((313/312; or 313,504; or (312/500) or (445/34)).CCLS.	USPAT	2003/06/12 15:58
237	(OLED organic adj3 el adj3 (device display).bi, and fET field adj effect adj transistor.bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/12 16:07
315	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).si, and (fET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/12 16:08
166	(OLED organic adj3 el adj3 (device display) organic adj1 (electroluminescent electroluminescence).si, and (fET field adj effect adj transistor).bi.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/06/12 16:08
98	((OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).si, and (fET field adj effect adj transistor).bi.) and (matrix matrices)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:09
52	((OLED organic adj3 el adj3 device display) organic adj1 (electroluminescent electroluminescence).bi, and (fET field adj effect adj transistor).bi.) and (matrix matrices); and (gas nitrogen krypton xenon argon neon helium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:16
36	((OLED organic adj3 el adj3 device display) organic adj1 (electroluminescent electroluminescence).bi, and (fET field adj effect adj transistor).bi.) and (matrix matrices); and (gas nitrogen krypton xenon argon neon helium) and (dry drying desiccant getter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:27
36	US-6111153-\$ cr US-6111113-\$ or US-6214510-\$ cr US-6104119-\$ cr US-6111117-\$ cr US-6146104-\$ cr US-6114037-\$ cr US-6114058-\$ cr US-6104571-\$ cr US-6104581-\$ cr US-6107546-\$ cr US-6443682-\$ cr US-6101415-\$ cr US-610444-\$ cr US-614152-\$ cr US-610455-\$ cr US-6104167-\$ cr US-641404-\$ cr US-6310358-\$ cr US-6104464-\$ cr US-6311010-\$ cr US-61046718-\$ cr US-6101126-\$ cr US-6101116-\$ cr US-631055-\$ cr US-6104594-\$).did. or US-6114215-\$ cr US-6510831-\$ cr US-6431130-\$ cr US-6443684-\$ cr US-6410715-\$ cr US-6410984-\$ cr US-6410714-\$ cr (EP-1089595-\$).did. or (EP-1083595-\$).did. or (EP-1083595-\$).did.	USPAT; EPO; JPO; DERWENT	2003/06/12 16:18

57 //US-6383664-\$ or US-3665238-\$ or
US-6210915-\$ or US-4204131-\$ or
US-5766053-\$ or US-5883464-\$ or
US-5997375-\$ or US-6037105-\$ or
US-6067932-\$ or US-6424032-\$ or
US-6154606-\$ or US-6380144-\$ or
US-6391110-\$ or US-6150111-\$ or
US-6351073-\$ or US-6358070-\$ or
US-6441551-\$ or US-6173156-\$ or
US-6184475-\$ or US-5560155-\$ or
US-1661964-\$ or US-5771800-\$ or
US-1831177-\$ or US-5864266-\$ or
US-1881701-\$ or US-1903051-\$).did. or
US-6372558-\$ or US-6112118-\$ or
US-6406591-\$ or US-6284141-\$ or
US-662941-\$ or US-6637607-\$ or
US-6645504-\$ or US-6181121-\$ or
US-6654672-\$ or US-6255163-\$ or
US-6661866-\$ or US-6127752-\$ or
US-4415148-\$ or US-6198145-\$ or
US-1317256-\$ or US-6438141-\$ or
US-1618790-\$ or US-6757116-\$ or
US-1618791-\$ or US-6018821-\$ or
US-1714101-\$ or US-6188111-\$ or
US-1814113-\$ or US-6411111-\$ or
US-611671-\$ or US-6111111-\$ or
US-64294122-\$).did. or US-6514700-\$ or
US-6516821-\$ or US-6522037-\$ or
US-6523343-\$ or US-64621410-\$ or
US-6461463-\$ or US-6448711-\$ or
US-6456121-\$ or US-6369167-\$ or
US-6149167-\$ or US-6411120-\$ or
US-6149167-\$ or US-6410719-\$).did. or
(US-13016068131-\$ or US-1301606117643-\$ or
US-1301607493-\$ or US-13020044746-\$ or
US-13016046574-\$ or US-13010650532-\$ or
US-130106018911-\$ or US-13020045397-\$ or
US-130106076-\$).did. or
(EP-130595-\$.did.) and organic

24 ((US 6283664-\$ or US-3665238-\$ or
US-421-15-\$ or US-4204721-\$ or
US-47-53-\$ or US-5683444-\$ or
US-59-178-\$ or US-603170-\$ or
US-62-132-\$ or US-64240-2-\$ or
US-63-16-2 or US-63801-2-\$ or
US-65-110-4 or US-61501-1-\$ or
US-67-178-4 or US-6-560-1-\$ or
US-441-81-\$ or US-6-751-1-\$ or
US-10-108-4 or US-5-851-1-\$ or
US-16-1-64-\$ or US-5-711-1-\$ or
US-18-1111-1 or US-5-64106-\$ or
US-18-1-161-1 or US-5-090151-\$).did. or
US-67-1508-\$ or US-610218-\$ or
US-41-1-91-\$ or US-6184341-\$ or
US-612341-\$ or US-6521741-\$ or
US-115314-\$ or US-6-153124-\$ or
US-65-4721-\$ or US-6553063-\$ or
US-4161666-\$ or US-4122131-\$ or
US-4312143-\$ or US-5306141-\$ or
US-6310136-\$ or US-5436141-\$ or
US-1496790-\$ or US-1757111-\$ or
US-10-1-111-\$ or US-1075634-\$ or
US-11-41-01-\$ or US-118-1-1-\$ or
US-11-1-111-\$ or US-11111-\$ or
US-11-1-1 or US-11111-\$ or
US-4294428-\$).did. or US-6115700-\$ or
US-61111-21-\$ or US-6921117-\$ or
US-612-133-\$ or US-8462471-\$ or
US-8422463-\$ or US-8448111-\$ or
US-1437120-\$ or US-6369677-\$ or
US-8143161-\$ or US-8411111-\$ or
US-8143911-\$ or US-8439111-\$).did. or
(US-109160068191-\$ or US-10020117643-\$ or
US-1111114934-\$ or US-1120044746-\$ or
US-111111046579-\$ or US-111110532-\$ or
US-111111018311-\$ or US-11120046397-\$ or
US-111111050781-\$).did. or
(EE-1133535-\$.did.; and organic) and (tft
field: adj effect adj3 transistor fet)

13 /((US-6363664-\$ or US-3665239-\$ or
US-6210815-\$ or US-4204721-\$ or
US-5766053-\$ or US-1383464-\$ or
US-5397378-\$ or US-1037710-\$ or
US-6061132-\$ or US-1424092-\$ or
US-6351106-\$ or US-1380588-\$ or
US-6751100-\$ or US-151181-\$ or
US-6751105-\$ or US-156021-\$ or
US-6441151-\$ or US-1771186-\$ or
US-5165465-\$ or US-15801636-\$ or
US-1661174-\$ or US-1771561-\$ or
US-5811177-\$ or US-1864206-\$ or
US-9141170-\$ or US-1809051-\$).did. or
US-6371518-\$ or US-6110518-\$ or
US-1610501-\$ or US-1843411-\$ or
US-6911121-\$ or US-1537688-\$ or
US-1537674-\$ or US-15511704-\$ or
US-15511712-\$ or US-15560649-\$ or
US-5165463-\$ or US-4121731-\$ or
US-1415141-\$ or US-1094233-\$ or
US-5311120-\$ or US-1431241-\$ or
US-6381130-\$ or US-1752126-\$ or
US-1011211-\$ or US-3019644-\$ or
US-1121111-\$ or US-1831111-\$ or
US-1311111-\$ or US-4111111-\$ or
US-1011111-\$ or US-1111111-\$ or
US-7401141-\$).did. or ((US-6511700-\$ or
US-1611161-\$ or US-1521170-\$ or
US-1521163-\$ or US-1461470-\$ or
US-1401480-\$ or US-1448110-\$ or
US-1431111-\$ or US-1369117-\$ or
US-1491111-\$ or US-1411110-\$ or
US-1411110-\$ or US-1439110-\$).did. or
(US-100.0117643-\$ or US-100.0117643-\$ or
US-1102.034746-\$ or US-1102.034746-\$ or
US-100.0116570-\$ or US-100.0116570-\$ or
US-100.0116811-\$ or US-100.0145397-\$ or
US-100.0150786-\$).did. or
(EP-1 10595-\$).did. and organic) and (tft
field ad² effect ad³ transistor fet)) and
(nitrogen krypton xenon argon neon helium)

USPAT; 2003/06/13 11:53
US-PGPUB;
EPO

1 (US-375445-\$).did.

USOCR 2003/06/13 11:53

-	69189 (313 'S'.CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/13 12:55
-	66840 (313 'S'.CCLS.	USPAT; EP ; JPO; DERWENT; IBM TDB	2003/06/13 12:55
-	0 ((31 'S .CCLS.) and tft with insulated adj gate &; field adj effect adj transistor	USPAT; EP ; JPO; IBM TDB	2003/06/13 12:56
-	464 tft with single adj4 (crystal crystalline) adj4 str; or.	USPAT; EP ; JPO; IBM TDB	2003/06/13 12:57
-	279 tft with single adj4 (crystal crystalline) adj4 str; or.	USPAT; EP; JPO; IBM TDB	2003/06/13 12:58
-	1 6433477.pn.	USPAT; US-PPGPUB; EPO; JPO; IBM TDB	2003/06/13 13:06
-	8 ("5643477" "5711824" "5834893" "588771" "5891264" "591352" "601411" "241130").did.	USPAT	2003/06/13 13:05
-	3 ("514111" "511134" "581893" "588771" "5891264" "591352" "601414" "824119").did.) and tft and gds	USPAT; US-PPGPUB; EPO; JPO; IBM TDB	2003/06/13 13:07
-	10 (US-6111724-4 or US-6534374-4 or US-6370383-3 or US-6512891-4 or US-6512894-3 or US-6512895-3 or US-6512896-3 or US-648219-3 or US-64821476-3 or US-64821477-3 or US-6441551-3 or US-6411041-3 or US-6411042-3 or US-6411043-3 or US-6411044-3 or US-6411045-3 or US-6411046-3 or US-6411047-3 or US-6411048-3 or US-6411049-3 or US-6411050-3 or US-6411051-3 or US-6411052-3 or US-6411053-3 or US-6411054-3 or US-6411055-3 or US-6411056-3 or US-6411057-3 or US-6411058-3 or US-6411059-3 or US-6411060-3 or US-6411061-3 or US-611411-4-3 or US-611411-5-3 or US-611411-6-3 or US-611411-7-3 or US-611411-8-3 or US-611411-9-3 or US-611411-10-3 or US-611411-11-3 or US-611411-12-3 or US-611411-13-3 or US-611411-14-3 or US-611411-15-3 or US-611411-16-3 or US-611411-17-3 or US-611411-18-3 or US-611411-19-3 or US-611411-20-3 or US-611411-21-3 or US-611411-22-3 or US-611411-23-3 or US-611411-24-3 or US-611411-25-3 or US-611411-26-3 or US-611411-27-3 or US-611411-28-3 or US-611411-29-3 or US-611411-30-3 or US-611411-31-3 or US-611411-32-3 or US-611411-33-3 or US-611411-34-3 or US-611411-35-3 or US-611411-36-3 or US-611411-37-3 or US-611411-38-3 or US-611411-39-3 or US-611411-40-3 or US-611411-41-3 or US-611411-42-3 or US-611411-43-3 or US-611411-44-3 or US-611411-45-3 or US-611411-46-3 or US-611411-47-3 or US-611411-48-3 or US-611411-49-3 or US-611411-50-3 or US-611411-51-3 or US-611411-52-3 or US-611411-53-3 or US-611411-54-3 or US-611411-55-3 or US-611411-56-3 or US-611411-57-3 or US-611411-58-3 or US-611411-59-3 or US-611411-60-3 or US-611411-61-3 or US-611411-62-3 or US-611411-63-3 or US-611411-64-3 or US-611411-65-3 or US-611411-66-3 or US-611411-67-3 or US-611411-68-3 or US-611411-69-3 or US-611411-70-3 or US-611411-71-3 or US-611411-72-3 or US-611411-73-3 or US-611411-74-3 or US-611411-75-3 or US-611411-76-3 or US-611411-77-3 or US-611411-78-3 or US-611411-79-3 or US-611411-80-3 or US-611411-81-3 or US-611411-82-3 or US-611411-83-3 or US-611411-84-3 or US-611411-85-3 or US-611411-86-3 or US-611411-87-3 or US-611411-88-3 or US-611411-89-3 or US-611411-90-3 or US-611411-91-3 or US-611411-92-3 or US-611411-93-3 or US-611411-94-3 or US-611411-95-3 or US-611411-96-3 or US-611411-97-3 or US-611411-98-3 or US-611411-99-3 or US-611411-100-3 or US-611411-101-3 or US-611411-102-3 or US-611411-103-3 or US-611411-104-3 or US-611411-105-3 or US-611411-106-3 or US-611411-107-3 or US-611411-108-3 or US-611411-109-3 or US-611411-110-3 or US-611411-111-3 or US-611411-112-3 or US-611411-113-3 or US-611411-114-3 or US-611411-115-3 or US-611411-116-3 or US-611411-117-3 or US-611411-118-3 or US-611411-119-3 or US-611411-120-3 or US-611411-121-3 or US-611411-122-3 or US-611411-123-3 or US-611411-124-3 or US-611411-125-3 or US-611411-126-3 or US-611411-127-3 or US-611411-128-3 or US-611411-129-3 or US-611411-130-3 or US-611411-131-3 or US-611411-132-3 or US-611411-133-3 or US-611411-134-3 or US-611411-135-3 or US-611411-136-3 or US-611411-137-3 or US-611411-138-3 or US-611411-139-3 or US-611411-140-3 or US-611411-141-3 or US-611411-142-3 or US-611411-143-3 or US-611411-144-3 or US-611411-145-3 or US-611411-146-3 or US-611411-147-3 or US-611411-148-3 or US-611411-149-3 or US-611411-150-3 or US-611411-151-3 or US-611411-152-3 or US-611411-153-3 or US-611411-154-3 or US-611411-155-3 or US-611411-156-3 or US-611411-157-3 or US-611411-158-3 or US-611411-159-3 or US-611411-160-3 or US-611411-161-3 or US-611411-162-3 or US-611411-163-3 or US-611411-164-3 or US-611411-165-3 or US-611411-166-3 or US-611411-167-3 or US-611411-168-3 or US-611411-169-3 or US-611411-170-3 or US-611411-171-3 or US-611411-172-3 or US-611411-173-3 or US-611411-174-3 or US-611411-175-3 or US-611411-176-3 or US-611411-177-3 or US-611411-178-3 or US-611411-179-3 or US-611411-180-3 or US-611411-181-3 or US-611411-182-3 or US-611411-183-3 or US-611411-184-3 or US-611411-185-3 or US-611411-186-3 or US-611411-187-3 or US-611411-188-3 or US-611411-189-3 or US-611411-190-3 or US-611411-191-3 or US-611411-192-3 or US-611411-193-3 or US-611411-194-3 or US-611411-195-3 or US-611411-196-3 or US-611411-197-3 or US-611411-198-3 or US-611411-199-3 or US-611411-200-3 or US-611411-201-3 or US-611411-202-3 or US-611411-203-3 or US-611411-204-3 or US-611411-205-3 or US-611411-206-3 or US-611411-207-3 or US-611411-208-3 or US-611411-209-3 or US-611411-210-3 or US-611411-211-3 or US-611411-212-3 or US-611411-213-3 or US-611411-214-3 or US-611411-215-3).did. or (US-611411-189-1-\$ or US-611411-17643-\$ or US-611411-45397-\$ or US-611411-4933-\$ or US-611411-134746-\$ or US-611411-1020068191-\$ or US-611411-160780-\$ or US-611411-1010046579-\$ or US-611411-160532-\$).did. r (EP-1 -.05-\$).didi.) and (tft) and single adj4 crystal crystalline)		2003/06/13 13:18

- 2 (6433487.pn. 6555969.pn.) and (tft; and
single adj3 (crystal crystalline) USPAT; 2003/06/13 13:20
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DERWENT;
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- 2 (6433487.pn. 6555969.pn.) and (tft) and
single adj3 (crystal crystalline) and
semiconductor adj2 film with (si silicon) USPAT; 2003/06/13 13:22
US-PGPUB;
EPO; JPO;
DERWENT;
IBM_TDE

- 2 (6433487.pn. 6555969.pn.) and active adj
matrix USPAT; 2003/06/13 14:58
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EPO; JPO;
DERWENT;
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